

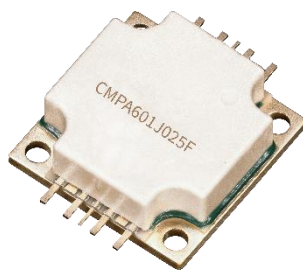
# CMPA601J025F

6 – 18 GHz, 25 W GaN HPA

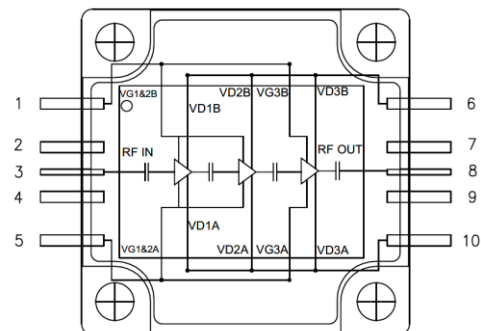
## Description

The CMPA601J025F is a 25 W, MMIC HPA utilizing the high performance, 0.15um GaN on SiC production process. The CMPA601J025F operates from 6 – 18 GHz and supports a variety of end applications such as electronic warfare, test instrumentation, radar and general amplification. The CMPA601J025F achieves 25 W of saturated output power with 20 dB of large signal gain and 20% power-added efficiency under CW operation.

Packaged in a 15x15 mm bolt-down, flange package, the CMPA601J025F provides superior broadband, RF performance and thermal management allowing customers to improve SWaP-C benchmarks in their next-generation systems.



**Figure 1. CMPA601J025F**



**Figure 2. Functional Block Diagram**

## Features

- Psat: 25 W
- PAE: 20 %
- LSG: 20 dB
- S21: 30 dB
- S11: -10 dB
- S22: -8 dB
- CW operation

## Applications

- Electronic Warfare
- Test Instrumentation
- Radar
- Broadband Amplifiers

Note: Features are typical performance across frequency under 25°C operation. Please reference performance charts for additional information.



### Absolute Maximum Ratings

| Parameter               | Symbol     | Units  | Value     | Conditions   |
|-------------------------|------------|--------|-----------|--------------|
| Drain to Source Voltage | $V_{DSS}$  | V      | 84        |              |
| Drain Voltage           | $V_D$      | V      | 22        |              |
| Gate Voltage            | $V_G$      | V      | -10, +2   |              |
| Drain Current           | $I_D$      | A      | 5.9       |              |
| Gate Current            | $I_G$      | mA     | 11        |              |
| Input Power             | $P_{in}$   | dBm    | 24        | CW operation |
| Dissipated Power        | $P_{diss}$ | W      | 130       |              |
| Storage Temperature     | $T_{stg}$  | °C     | -55, +150 |              |
| Mounting Temperature    | $T_J$      | °C     | 320       | 30 seconds   |
| Junction Temperature    | $T_J$      | °C     | 225       | MTTF > 1E6   |
| Output Mismatch Stress  | VSWR       | $\Psi$ | 3:1       |              |

### Recommended Operating Conditions

| Parameter        | Symbol     | Units | Typical Value | Conditions        |
|------------------|------------|-------|---------------|-------------------|
| Drain Voltage    | $V_d$      | V     | 22            |                   |
| Gate Voltage     | $V_g$      | V     | -1.9          |                   |
| Drain Current    | $I_{dq}$   | mA    | >1.2          |                   |
| Input Power      | $P_{in}$   | dBm   | 24            | CW operation only |
| Case Temperature | $T_{case}$ | °C    | -40 to 60     |                   |

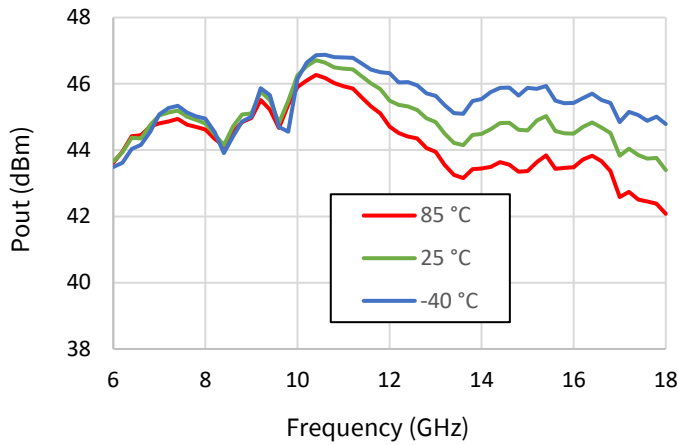
### RF Specifications

Test conditions unless otherwise noted:  $V_d=22V$ ,  $I_{dq}= 1200mA$ , CW,  $P_{in} = 24dBm$ ,  $T_{base}=25^\circ C$ , Frequency: 12GHz

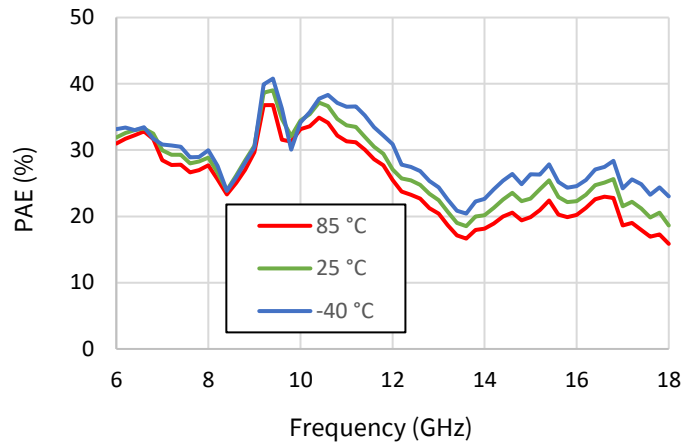
| Parameter              | Units | Frequency | Min | Typical | Max | Conditions    |
|------------------------|-------|-----------|-----|---------|-----|---------------|
| Frequency              | GHz   |           | 6   |         | 18  |               |
| Output Power           | dBm   | 6         |     | 43.5    |     |               |
|                        |       | 12        |     | 45.0    |     |               |
|                        |       | 18        |     | 43.0    |     |               |
| Power-added Efficiency | %     | 6         |     | 33      |     |               |
|                        |       | 12        |     | 27      |     |               |
|                        |       | 18        |     | 19      |     |               |
| LSG                    | dB    | 6         |     | 19.5    |     |               |
|                        |       | 12        |     | 21.0    |     |               |
|                        |       | 18        |     | 19      |     |               |
| Small-Signal Gain      | dB    | 6         |     | 31      |     | Pin = -25 dBm |
|                        |       | 12        |     | 30      |     |               |
|                        |       | 18        |     | 26      |     |               |
| Input Return Loss      | dB    |           |     | -10     |     | Pin = -25 dBm |
| Output Return Loss     | dB    |           |     | -8      |     | Pin = -25 dBm |

Test conditions unless otherwise noted:  $V_d=22V$ ,  $I_{dq}=1200mA$ , CW,  $P_{in}=24dBm$ ,  $T_{base}=25^\circ C$ , Frequency: 12GHz

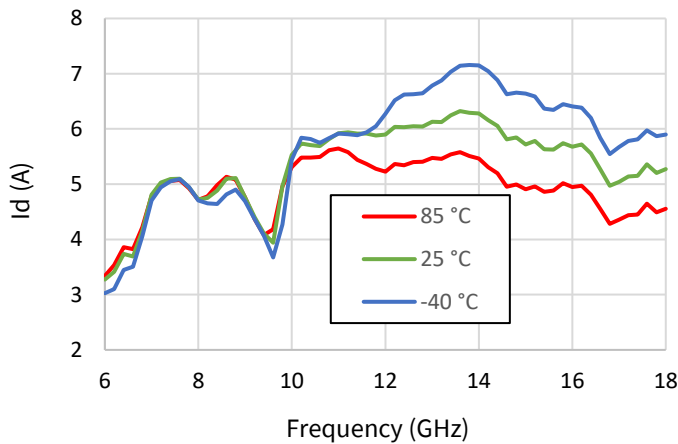
**Figure 3: Pout v. Frequency v. Temperature**



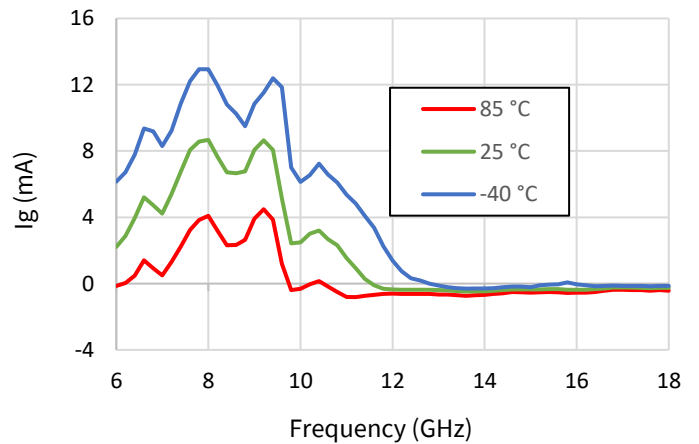
**Figure 4: PAE v. Frequency v. Temperature**



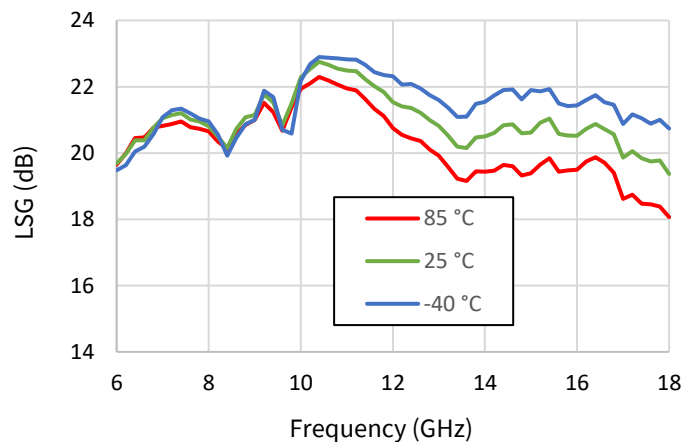
**Figure 5: Id v. Frequency v. Temperature**



**Figure 6: Ig v. Frequency v. Temperature**

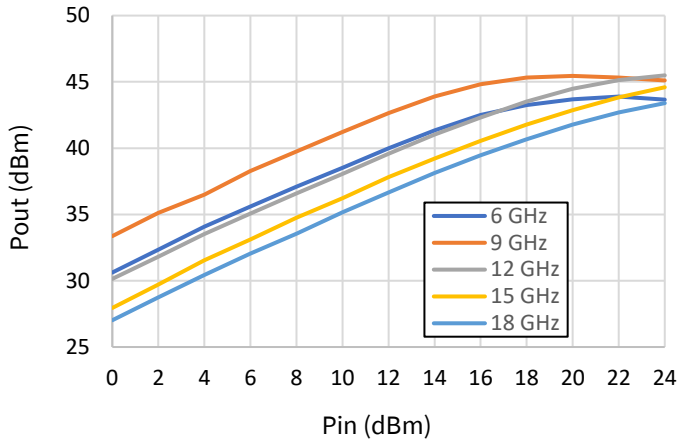


**Figure 7: LSG v. Frequency v. Temperature**

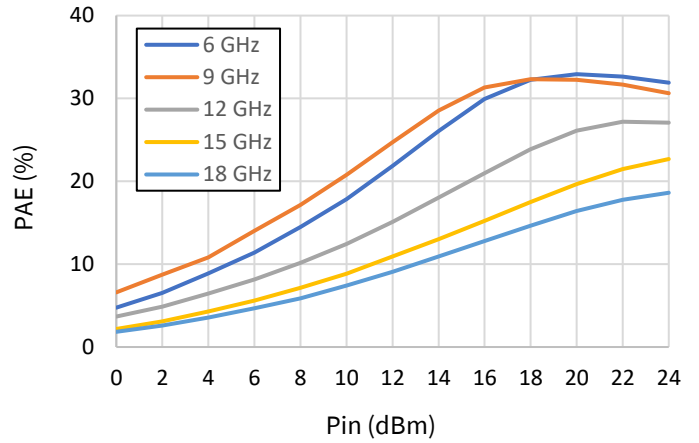


Test conditions unless otherwise noted:  $V_d=22V$ ,  $I_{dq}=1200mA$ , CW,  $P_{in}=24dBm$ ,  $T_{base}=25^\circ C$ , Frequency: 12GHz

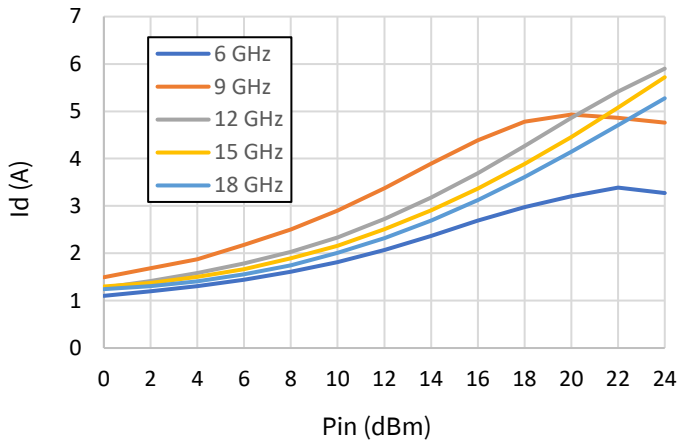
**Figure 8: Pout v. Pin v. Frequency**



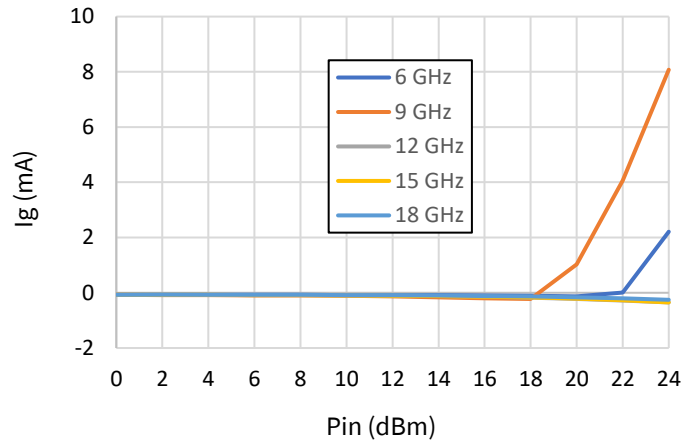
**Figure 9: PAE v. Pin v. Frequency**



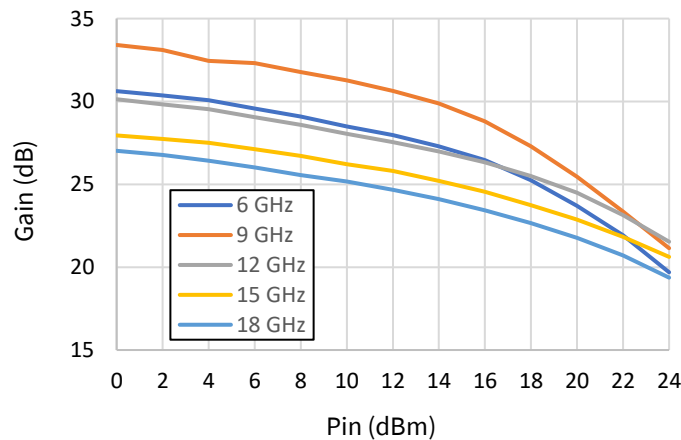
**Figure 10: Id v. Pin v. Frequency**



**Figure 11: Ig v. Pin v. Frequency**

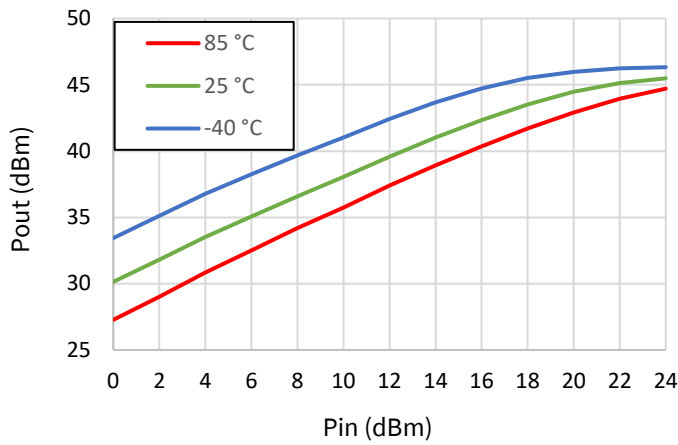


**Figure 12: Gain v. Pin v. Frequency**

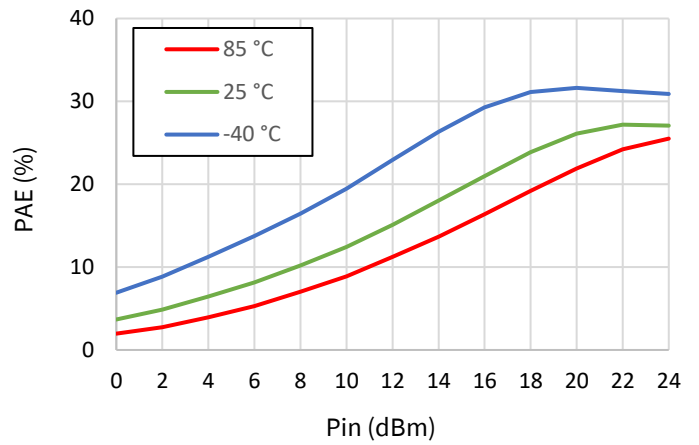


Test conditions unless otherwise noted:  $V_d=22V$ ,  $I_{dq}=1200mA$ , CW,  $P_{in}=24dBm$ ,  $T_{base}=25^\circ C$ , Frequency: 12GHz

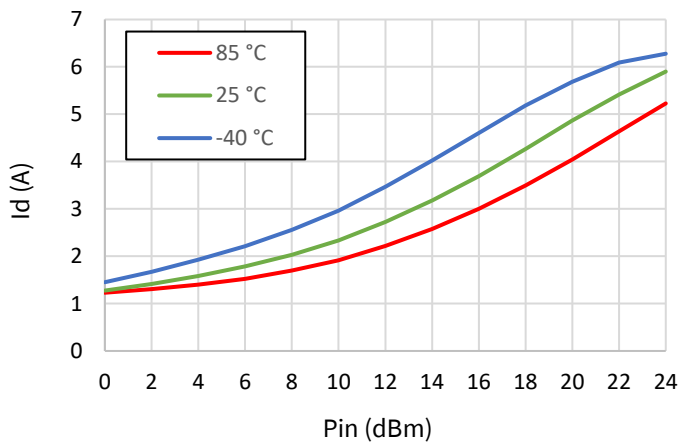
**Figure 13: Pout v. Pin v. Temperature**



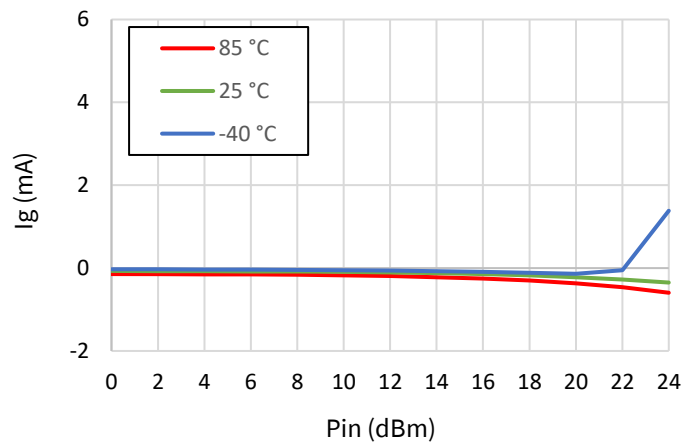
**Figure 14: PAE v. Pin v. Temperature**



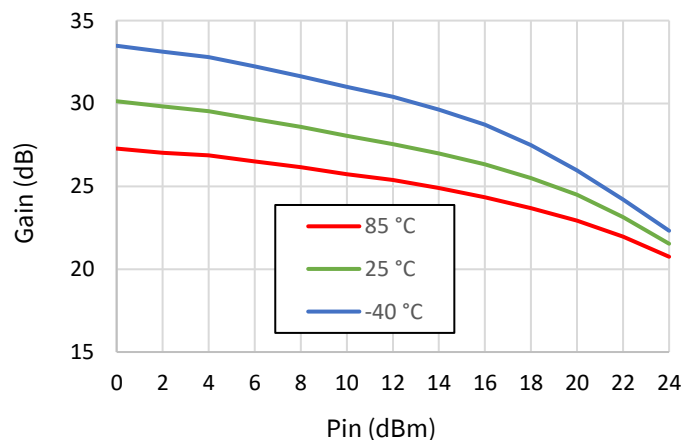
**Figure 15: Id v. Pin v. Temperature**



**Figure 16: Ig v. Pin v. Temperature**

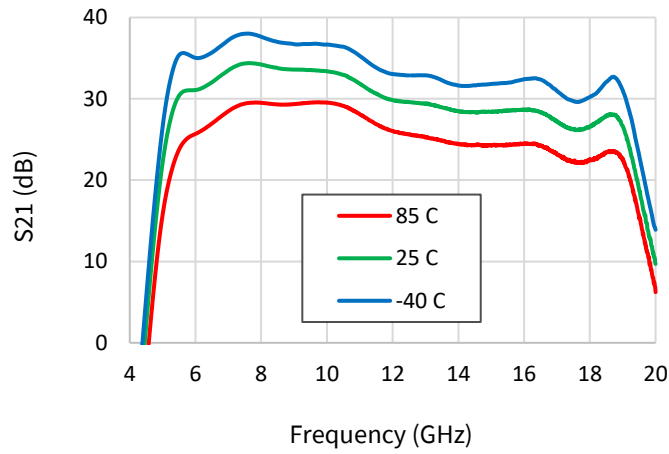


**Figure 17: Gain v. Pin v. Temperature**

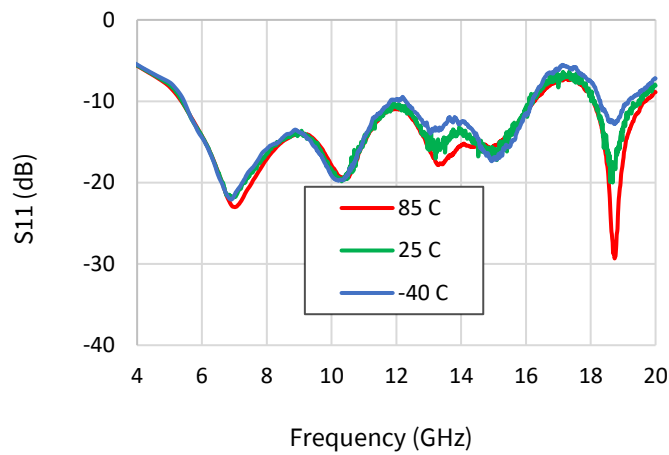


Test conditions unless otherwise noted:  $V_d=22V$ ,  $I_{dq}=1200mA$ ,  $P_{in}=-25dBm$ ,  $T_{base}=25^\circ C$

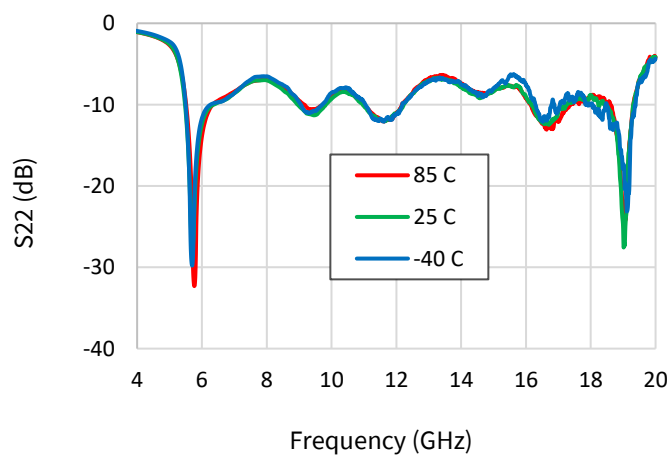
**Figure 18: S21 v. Frequency v. Temperature**



**Figure 19: S11 v. Frequency v. Temperature**



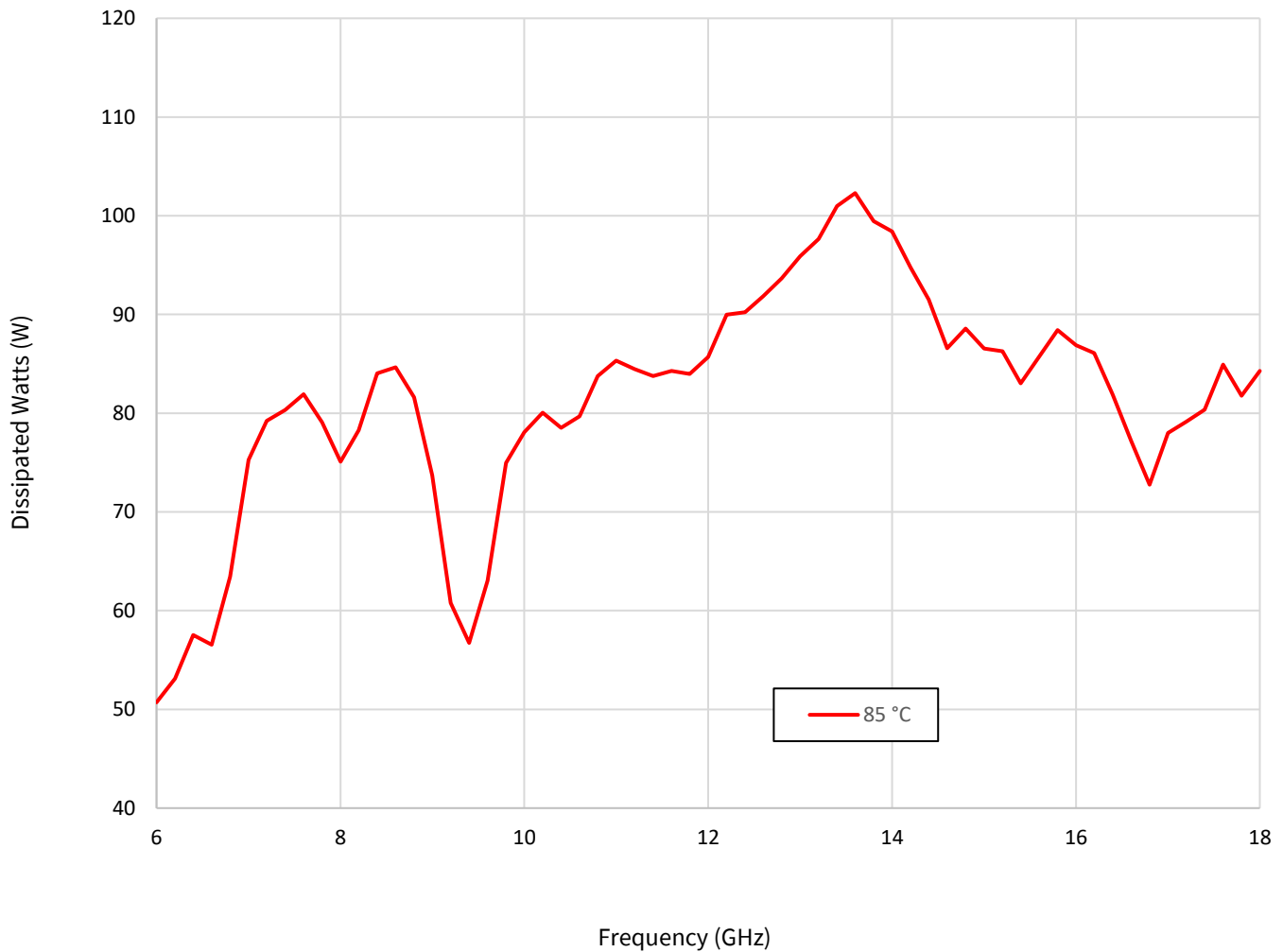
**Figure 20: S22 v. Frequency v. Temperature**



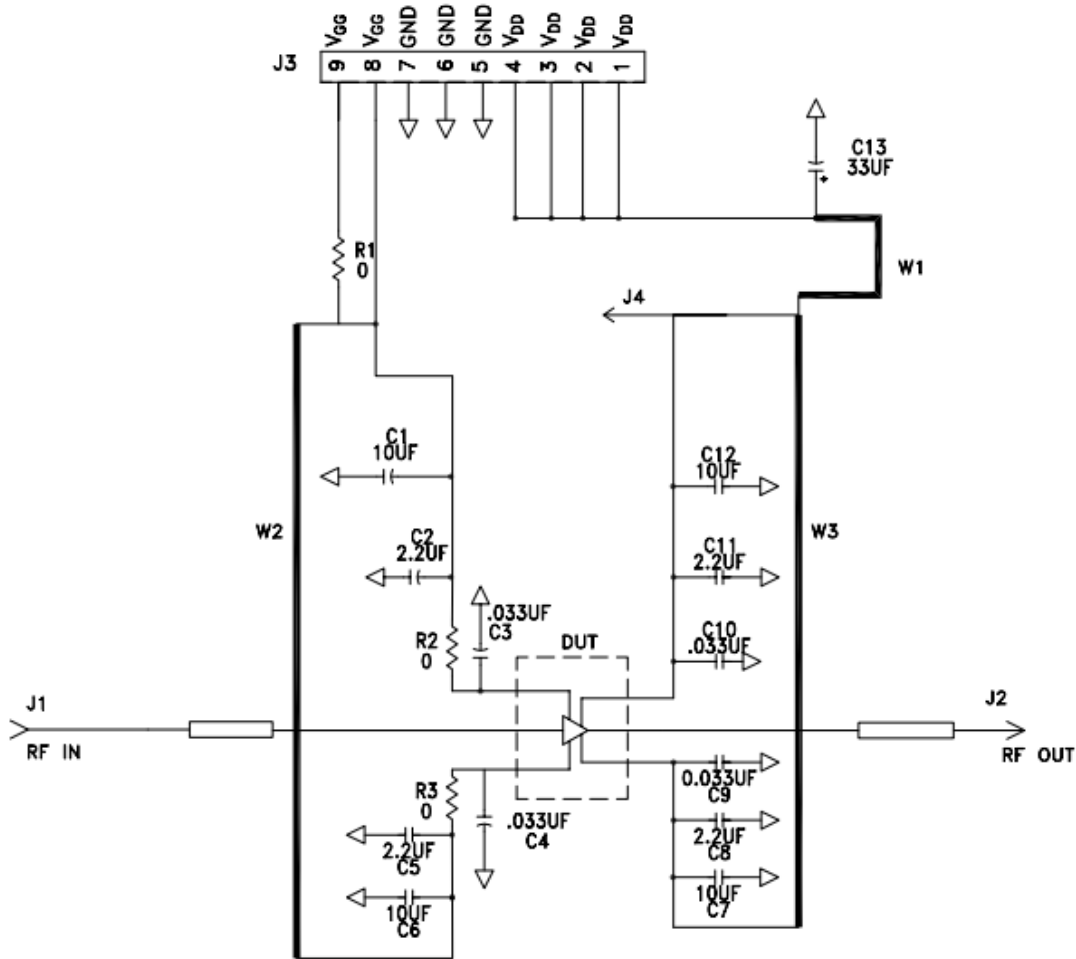
**Thermal Characteristics**

| Parameter                            | Symbol          | Value    | Operating Conditions  |
|--------------------------------------|-----------------|----------|---|
| Operating Junction Temperature       | $T_J$           | 231°C    | Freq = 13.6 GHz, $V_d = 22$ V, $I_{dq} = 1.2$ A, $I_{drive} = 5.6$ A,<br>$P_{in} = 24$ dBm, $P_{out} = 43.2$ dBm, $P_{diss} = 102$ W, $T_{case} = 60^\circ\text{C}$ ,<br>CW |
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 1.68°C/W |   |

**Power Dissipation v. Frequency ( $T_{case} = 60^\circ\text{C}$ )**



**CMPA601J025F-AMP Evaluation Board Schematic Drawing**

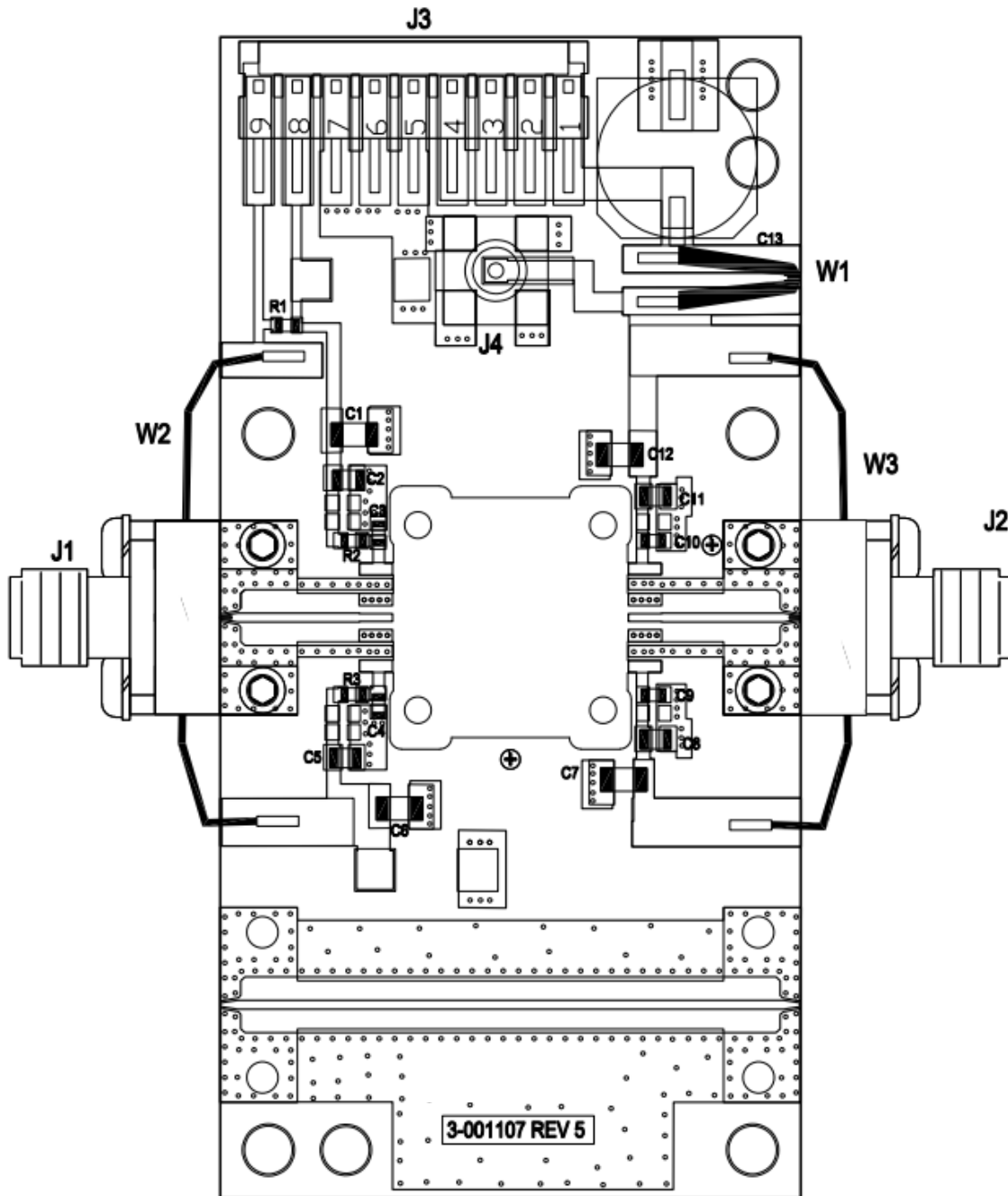


**CMPA601J025F-AMP Evaluation Board Bill of Materials**

| Reference Designator | Description   | Qty |
|----------------------|---|-----|
| R1,R2,R3             | RES 0.0 OHM 1/10W 0603 SMD                                  | 3   |
| C1,C6,C7,C12         | CAP, 10uF, +/-10%, 50V, 1206                                | 4   |
| C2,C5,C8,C11         | CAP, 2.2uF, +/-10%, 50V, 0805                               | 4   |
| C13                  | CAP, 33 uF, 20%, 100V, ELECTROLYTIC                         | 1   |
| C3,C4,C9,C10         | CAP, .033uF, 50V,0603                                       | 4   |
| -                    | PCB, RO3003, .010 THK, HPHF Package                         | 1   |
| -                    | BASEPLATE 3.0x1.5x0.25Cu                                    | 1   |
| J1,J2                | CONN, SMA JACK (FEMALE) END LAUNCH CONNECTOR                | 2   |
| J4                   | CONN, SMB, STRAIGHT JACK RECEPTACLE, SMT, 50 OHM, Au PLATED | 2   |
| J3                   | HEADER RT>PLZ .1CEN LK 9POS                                 | 1   |
| W1                   | WIRE, BLACK, 30 AWG   | 1   |
| W2,W3                | WIRE, BLACK, 22 AWG   | 2   |
| U1                   | CMPA601J025F  | 1   |



**CMPA601J025F-AMP Evaluation Board Assembly Drawing**



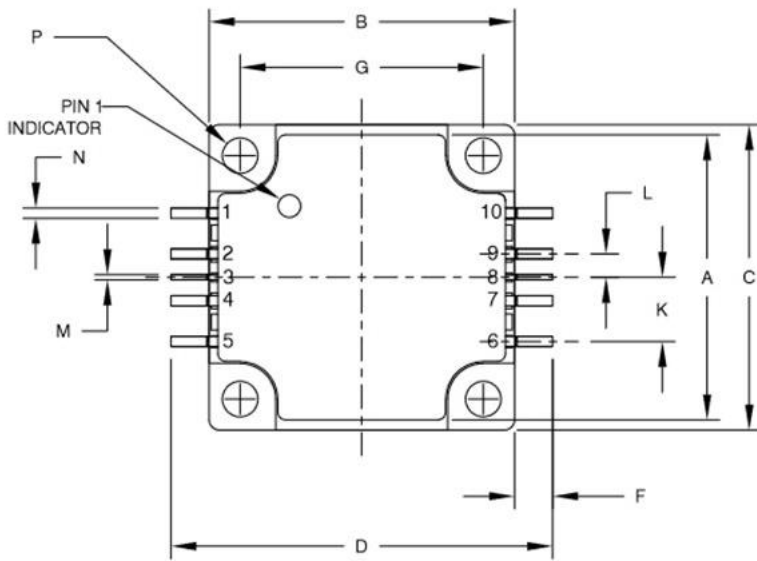
**Bias On Sequence**

1. Ensure RF is turned-off
2. Apply pinch-off voltage of -5 V to the gate ( $V_g$ )
3. Apply nominal drain voltage ( $V_d$ )
4. Adjust  $V_g$  to obtain desired quiescent drain current ( $I_{dq}$ )
5. Apply RF

**Bias Off Sequence**

1. Turn RF off
2. Apply pinch-off to the gate ( $V_g=-5V$ )
3. Turn off drain voltage ( $V_d$ )
4. Turn off gate voltage ( $V_g$ )

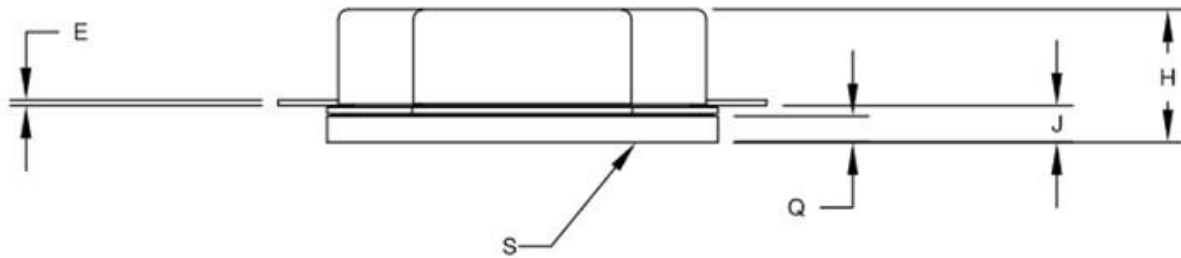
**Product Dimensions**



NOTES: UNLESS OTHERWISE SPECIFIED

1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.

| DIM | INCHES |        |      | MILLIMETERS |         |       |
|-----|--------|--------|------|-------------|---------|-------|
|     | MIN    | TYP    | MAX  | MIN         | TYP     | MAX   |
| A   | .555   | .560   | .565 | 14.10       | 14.22   | 14.35 |
| B   | .595   | .600   | .605 | 15.11       | 15.24   | 15.37 |
| C   | .595   | .600   | .605 | 15.11       | 15.24   | 15.37 |
| D   | -      | (.750) | -    | -           | (19.05) | -     |
| E   | .006   | .008   | .010 | 0.15        | 0.20    | 0.25  |
| F   | .065   | .075   | .085 | 1.66        | 1.91    | 2.16  |
| G   | .473   | .478   | .483 | 12.01       | 12.14   | 12.27 |
| H   | .191   | .203   | .215 | 4.86        | 5.16    | 5.46  |
| J   | .049   | .056   | .063 | 1.24        | 1.42    | 1.60  |
| K   | .121   | .126   | .131 | 3.07        | 3.20    | 3.33  |
| L   | .041   | .046   | .051 | 1.04        | 1.17    | 1.30  |
| M   | .005   | .010   | .015 | 0.13        | .25     | 0.38  |
| N   | .015   | .020   | .025 | 0.38        | .51     | 0.63  |
| P   | .065   | .070   | .075 | 1.65        | 1.78    | 1.90  |
| Q   | .038   | .040   | .042 | 0.97        | 1.02    | 1.07  |




| PIN | DESC. | PIN | DESC.  |
|-----|-------|-----|--------|
| 1   | VG    | 6   | VD     |
| 2   | GND   | 7   | GND    |
| 3   | RF IN | 8   | RF OUT |
| 4   | GND   | 9   | GND    |
| 5   | VG    | 10  | VD     |

## Electrostatic Discharge (ESD) Classification

| Parameter           | Symbol | Class | Classification Level           | Test Methodology    |
|---------------------|--------|-------|--------------------------------|---------------------|
| Human body Model    | HBM    | TBD   | ANSI/ESDA/JEDEC JS-001 Table 3 | JEDEC JESD22 A114-D |
| Charge Device Model | CDM    | TBD   | ANSI/ESDA/JEDEC JS-002 Table 3 | JEDEC JESD22 C101-C |

## Product Ordering Information

| Part Number      | Description              | MOQ Increment | Image   |
|------------------|--------------------------|---------------|---|
| CMPA601J025F     | 6 – 18 GHz, 25W GaN MMIC |               |  |
| CMPA601J025F-AMP | Evaluation Board w/ PA   | 1 Each        |   |

## Notes & Disclaimer

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